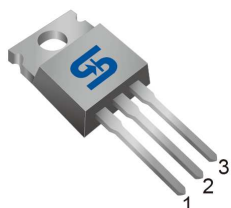
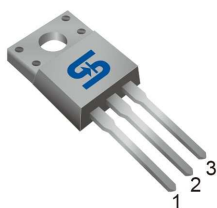


TO-220



ITO-220



**Pin Definition:**

1. Gate
2. Drain
3. Source

**PRODUCT SUMMARY**

$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
800	3 @ $V_{GS}=10V$	4

**General Description**

The TSM4N80 N-Channel enhancement mode Power MOSFET is produced by planar stripe DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switch mode power supply, electronic lamp ballast based on half bridge.

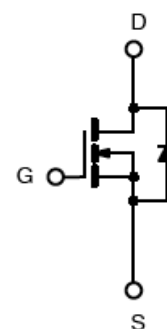
**Features**

- Low  $R_{DS(ON)}$  3 $\Omega$  (Max.)
- Low gate charge typical @ 25nC (Typ.)
- Improve dv/dt capability

**Ordering Information**

Part No.	Package	Packing
TSM4N80CZ C0	TO-220	50pcs / Tube
TSM4N80CI C0	ITO-220	50pcs / Tube

**Block Diagram**



N-Channel MOSFET

**Absolute Maximum Rating** ( $T_a = 25^\circ C$  unless otherwise noted)

Parameter	Symbol	TO-220	ITO-220	Unit
Drain-Source Voltage	$V_{DS}$	800		V
Gate-Source Voltage	$V_{GS}$	$\pm 30$		V
Continuous Drain Current	$I_D$	$T_c = 25^\circ C$	4	4 *
		$T_c = 100^\circ C$	2.5	2.5 *
Pulsed Drain Current *	$I_{DM}$	16	16 *	A
Peak Diode Recovery dv/dt (Note 3)	dv/dt	4.5		V
Single Pulse Avalanche Energy (Note 2)	$E_{AS}$	474		mJ
Avalanche Current (Repetitive) (Note 1)	$I_{AR}$	4		A
Repetitive Avalanche Energy (Note 1)	$E_{AR}$	12.3		mJ
Power Dissipation	$P_D$	$T_c = 25^\circ C$	123	38.7
		Derate above 25 $^\circ C$	0.98	0.3
Operating Junction Temperature	$T_J$	150		$^\circ C$
Storage Temperature Range	$T_{STG}$	-55 to +150		$^\circ C$

\* Limited by maximum junction temperature

### Thermal Performance

Parameter	Symbol	TO-220	ITO-220	Unit
Thermal Resistance - Junction to Case	$R_{\theta_{JC}}$	1.01	3.23	°C/W
Thermal Resistance - Junction to Ambient	$R_{\theta_{JA}}$	62.5		

Notes: Surface mounted on FR4 board  $t \leq 10\text{sec}$

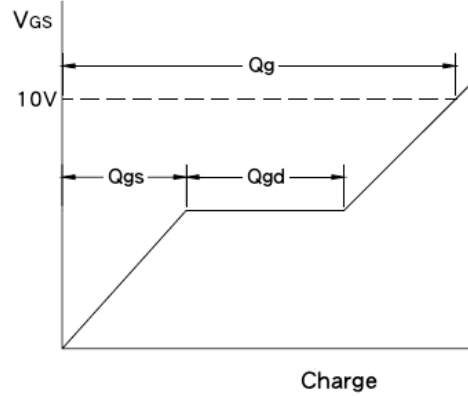
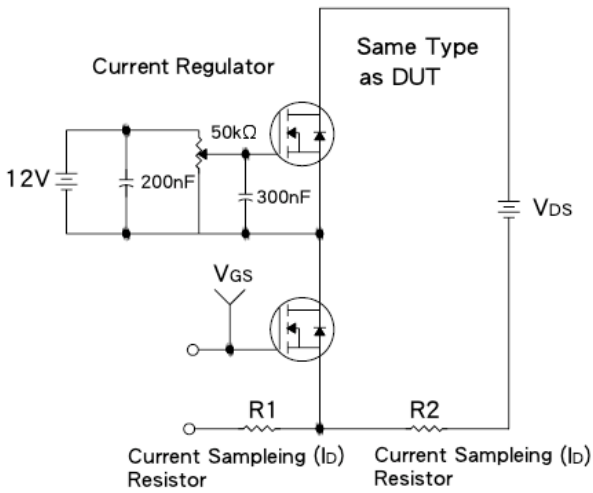
### Electrical Specifications ( $T_c = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu\text{A}$	$BV_{DSS}$	800	--	--	V
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 2.0A$	$R_{DS(ON)}$	--	2.5	3.0	$\Omega$
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	$V_{GS(TH)}$	2.0	--	4.0	V
Zero Gate Voltage Drain Current	$V_{DS} = 800V, V_{GS} = 0V$	$I_{DSS}$	--	--	10	$\mu\text{A}$
Gate Body Leakage	$V_{GS} = \pm 30V, V_{DS} = 0V$	$I_{GSS}$	--	--	$\pm 100$	nA
Forward Transconductance	$V_{DS} = 30V, I_D = 2.0A$	$g_{fs}$	--	7.1	--	S
Diode Forward Voltage	$I_S = 4A, V_{GS} = 0V$	$V_{SD}$	--	--	1.5	V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	$V_{DS} = 640V, I_D = 4A, V_{GS} = 10V$	$Q_g$	--	20	--	nC
Gate-Source Charge		$Q_{gs}$	--	3.7	--	
Gate-Drain Charge		$Q_{gd}$	--	8.2	--	
Input Capacitance	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0\text{MHz}$	$C_{iss}$	--	955	--	pF
Output Capacitance		$C_{oss}$	--	80	--	
Reverse Transfer Capacitance		$C_{rss}$	--	13	--	
<b>Switching<sup>c</sup></b>						
Turn-On Delay Time	$V_{GS} = 10V, I_D = 4A, V_{DD} = 400V, R_G = 25\Omega$	$t_{d(on)}$	--	49	--	nS
Turn-On Rise Time		$t_r$	--	38	--	
Turn-Off Delay Time		$t_{d(off)}$	--	146	--	
Turn-Off Fall Time		$t_f$	--	50	--	
Reverse Recovery Time	$V_{GS} = 0V, I_S = 4A,$	$t_{fr}$	--	487	--	nS
Reverse Recovery Charge	$di_F/dt = 100A/\mu\text{s}$	$Q_{fr}$	--	2.8	--	$\mu\text{C}$

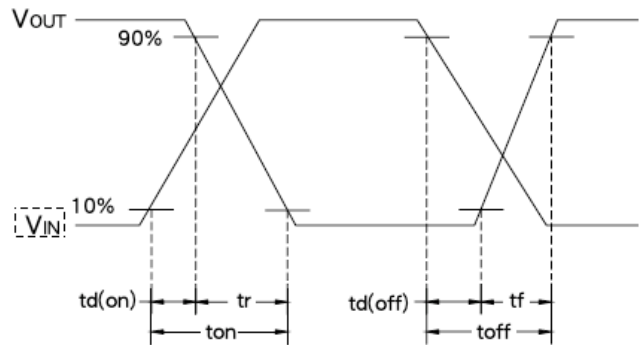
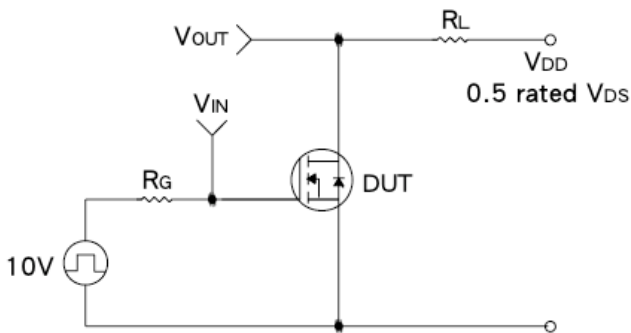
#### Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2.  $V_{DD} = 50V, I_{AS} = 4A, L = 56\text{mH}, R_G = 25\Omega, \text{Starting } T_J = 25^\circ\text{C}$
3.  $I_{SD} \leq 8A, di/dt \leq 200A/\mu\text{s}, V_{DD} \leq BV, \text{Starting } T_J = 25^\circ\text{C}$
4. Pulse test: pulse width  $\leq 300\mu\text{s}$ , duty cycle  $\leq 2\%$
5. b For design reference only, not subject to production testing.
6. c Switching time is essentially independent of operating temperature.

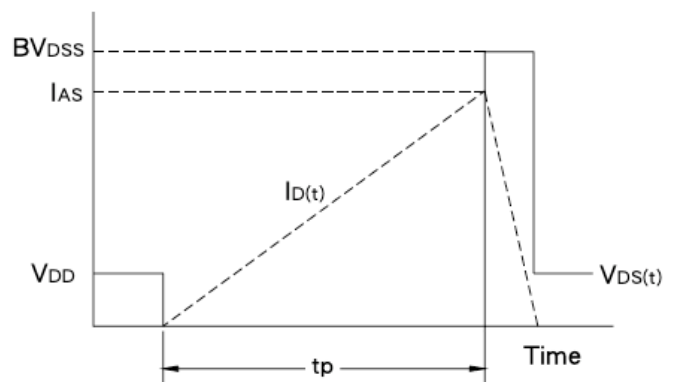
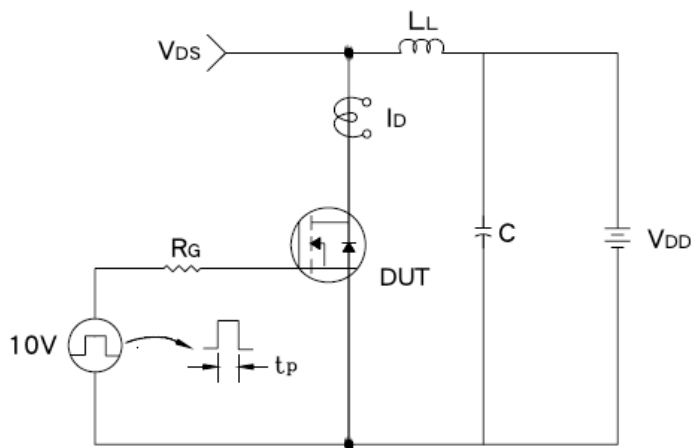
### Gate Charge Test Circuit & Waveform



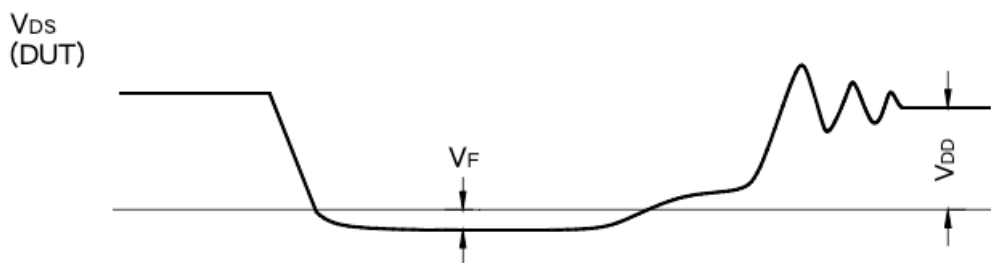
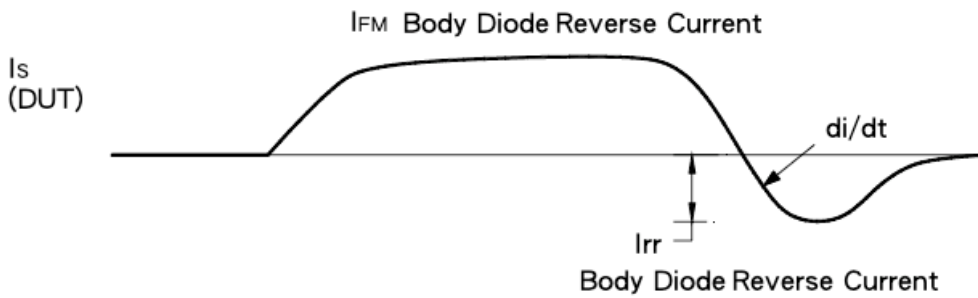
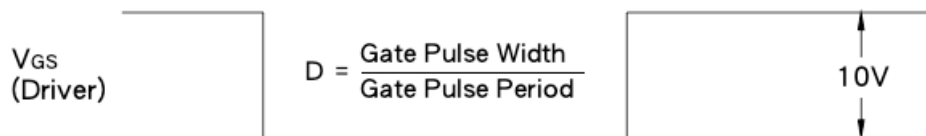
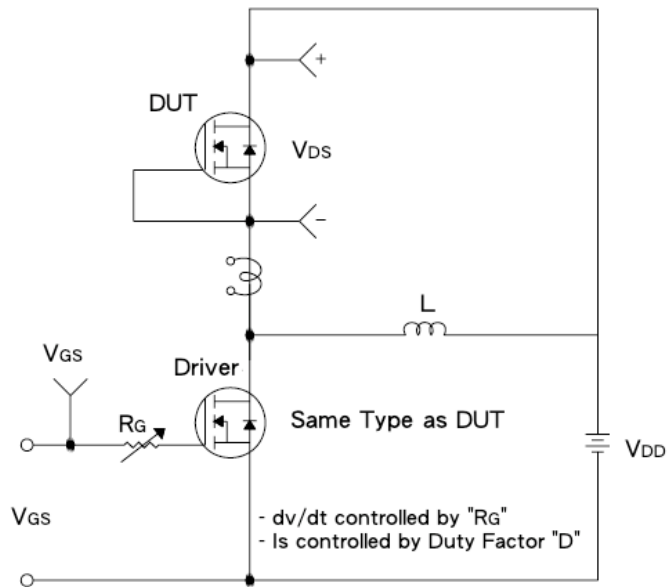
### Resistive Switching Test Circuit & Waveform



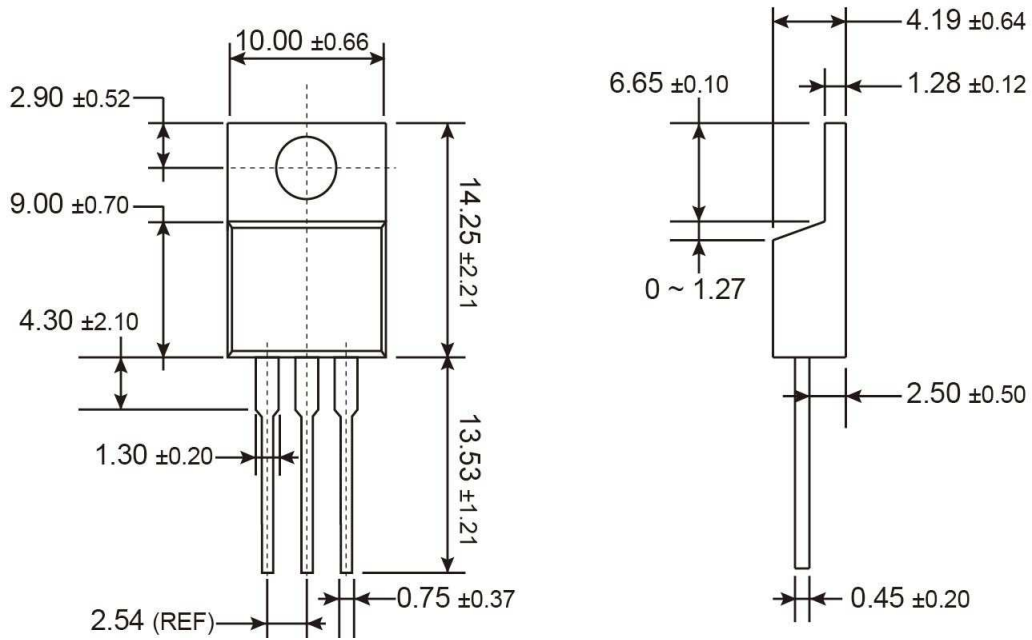
### E<sub>AS</sub> Test Circuit & Waveform



**Diode Reverse Recovery Time Test Circuit & Waveform**

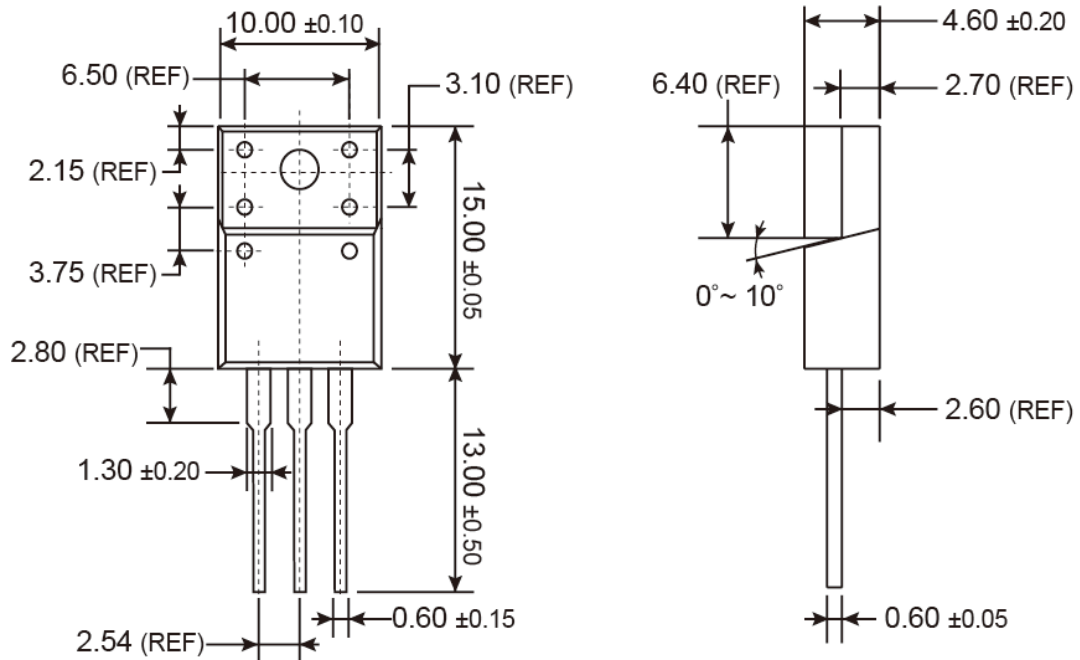


### TO-220 Mechanical Drawing



Unit: Millimeters

### ITO-220 Mechanical Drawing



Unit: Millimeters

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